

# NPN SILICON LOW NOISE RF TRANSISTOR

**DESCRIPTION:**

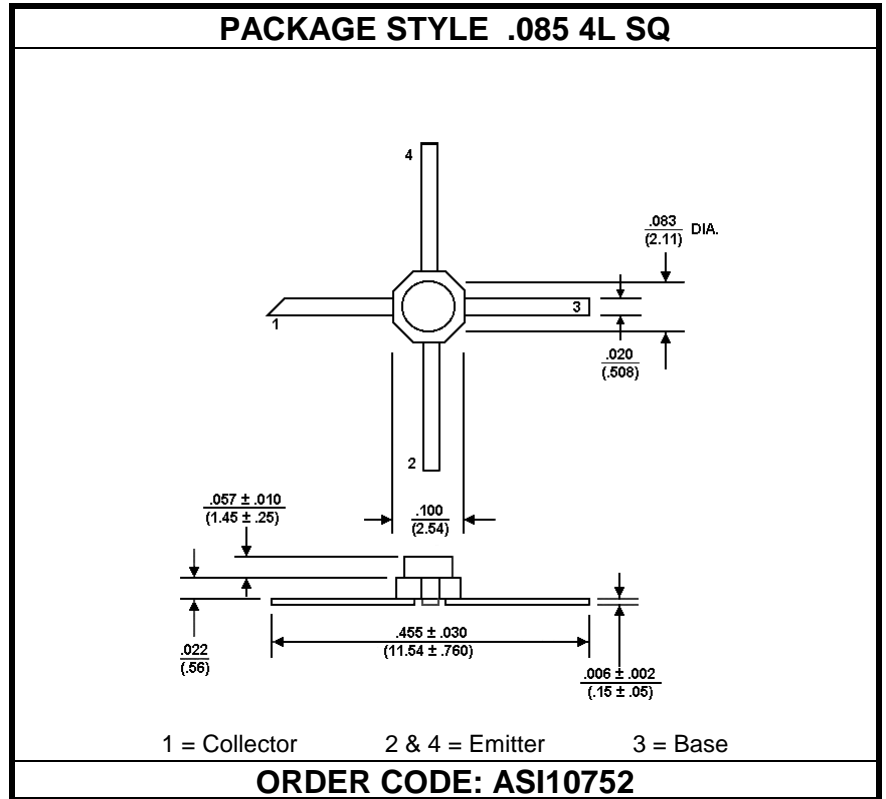
The **ASI NE64535** is a Common Emitter Device Designed for Low Noise Class A Amplifier Applications up to 4.0 GHz.

**FEATURES INCLUDE:**

- $N_F = 1.6$  dB Typical @ 2 GHz
- $|S_{21E}|^2 = 11$  dB Typical @ 2 GHz
- Hermetic Ceramic Package

**MAXIMUM RATINGS:**

$I_C$	60 mA
$V_{CB0}$	25 V
$V_{CEO}$	12 V
$V_{EBO}$	1.5 V
$P_{DISS}$	300 mW @ $T_A \leq 75^\circ\text{C}$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	85 °C/W


**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$I_{CB0}$	$V_{CB} = 8$ V					100	nA
$I_{EBO}$	$V_{EB} = 1.0$ V					1.0	$\mu\text{A}$
$h_{FE}$	$V_{CE} = 8.0$ V	$I_C = 7.0$ mA		50		250	---
$C_{CB}$	$V_{CB} = 10$ V					0.6	pF
$f_t$	$V_{CE} = 10$ V	$I_C = 20$ mA	$f = 1.0$ GHz	8.0	8.5		GHz
$ S_{21E} ^2$	$V_{CE} = 8$ V	$I_C = 20$ mA	$f = 2.0$ GHz	10	11		dB
<b>NF</b> <b>GA</b>	$V_{CE} = 8$ V	$I_C = 10$ mA	$f = 2.0$ GHz	10	1.6 11	2.5	dB



*A D V A N C E D S E M I C O N D U C T O R , I N C .*

*7525 ETHEL AVENUE • NORTH HOLLYWOOD, CA 91605 • (818) 982-1202 • TELEX: 18-2651 • FAX (818) 765-3004*